

Please add the following new claims:

15 (New) } A method for etching a pattern in an etching body in accordance with a plasma, comprising the steps of:

coupling at least temporarily a high-frequency-pulsed high-frequency power into the etching body via an at least temporarily applied high-frequency a.c. voltage; and modulating the coupled, high-frequency-pulsed high-frequency power is modulated at a low frequency.

16 (New) } The method of claim 15, wherein:
the etching pattern is a cut-out,
the etching body is a silicon body, and
the cut-outs are exactly defined by an etching mask in a lateral manner.

17 (New) } The method of claim 15, wherein the at least temporarily applied high-frequency a.c. voltage is provided by a high-frequency generator, the high-frequency generator generating a high-frequency carrier signal.

18 (New) } The method of claim 15, wherein the high-frequency-pulsed high-frequency power is pulsed at a frequency of 10 kHz to 500 kHz.

19 (New) } The method of claim 18, wherein the high-frequency-pulsed high-frequency power is pulsed at a frequency of 50 kHz to 200 kHz.

20 (New) } The method of claim 17, wherein the high-frequency carrier signal has a frequency of 1 MHz to 50 MHz.

21 (New) } The method of claim 20, wherein the high-frequency carrier signal has a frequency of 13.56 MHz.

21 (New) The method of claim 17, wherein the high-frequency generator generates a high-frequency power having an amplitude of 30 watts to 1200 watts.

23 (New) The method of claim 22, wherein the high-frequency generator generates a high-frequency power having an amplitude of 50 watts to 500 watts.

24 (New) The method of claim 15, wherein the high-frequency-pulsed high-frequency power is coupled in the form of square-wave pulses.

25 (New) The method of claim 24, wherein the square-wave pulses have a rise time of clock pulse edges of the square-wave pulses of less than 0.3 μ s.

26 (New) The method of claim 15, wherein a mark-to-space ratio of the high-frequency-pulsed high-frequency power is between 1:1 and 1:100.

27 (New) The method of claim 26, wherein the mark-to-space ratio of the high-frequency-pulsed high-frequency power is between 1:2 and 1:19.

28 (New) The method of claim 15, wherein a sequence of pulses of the high-frequency-pulsed power and pulse intervals corresponds to an average high-frequency power of 1 watt to 100 watts.

29 (New) The method of claim 15, wherein the coupled, high-frequency-pulsed high-frequency power is periodically modulated using a low-frequency clocking.

30 (New) The method of claim 15, wherein one of a low-frequency clocking and the low-frequency modulation is performed at a frequency of 10 Hz to 10000 Hz.

31 (New) The method of claim 30, wherein the one of the low-frequency clocking and the low-frequency modulation is performed at a frequency of 50 Hz to 1000 Hz.